

2N398, 2N398 A (GERMANIUM)

**CASE 31(1)
(TO-5)**

All leads isolated



PNP germanium transistor for high-voltage, audio-frequency applications.

MAXIMUM RATINGS

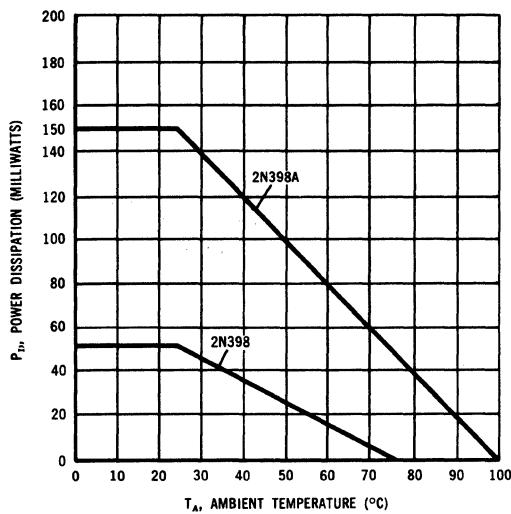
Rating	Symbol	2N398A	2N398	Unit
Collector-Base Voltage	V_{CB}	105	105	Vdc
Collector-Emitter Voltage	V_{CEO}	105	105	Vdc
Emitter-Base Voltage	V_{EB}	50	50	Vdc
DC Collector Current	I_C	200	100	mA
Emitter Current	I_E	200	100	mA
Junction Temperature	T_J	-65 to +100	-65 to +85	°C
Storage Temperature	T_{stg}	-65 to +100	-65 to +85	°C
Collector Dissipation @ 25°C	P_D	150	50	mW
Thermal Resistance, Junction to Ambient	$\theta_{JA \text{ max}}$	0.5	1.2	°C/mW

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

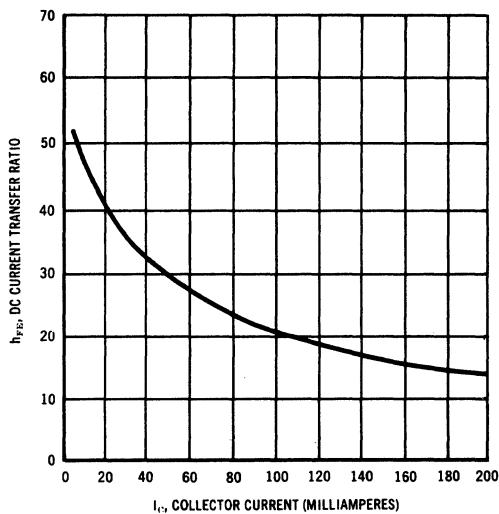
Characteristics	Symbol	Min	Typical	Max	Unit
Collector-Base Cutoff Current ($V_{CB} = 105$ V, $I_B = 0$)	I_{CBO}	-	12.0	50	μA
Collector-Base Cutoff Current ($V_{CB} = 2.5$ V, $I_B = 0$)	I_{CBO}	-	5.0	14	μA
Emitter-Base Cutoff Current ($V_{EB} = 50$ V, $I_C = 0$)	I_{EBO}	-	3.0	50	μA
Collector-Emitter Saturation Voltage ($I_C = 5$ mAdc; $I_B = 0.25$ mAdc)	$V_{CE \text{ (SAT)}}$	-	0.11	0.35	Vdc
Base-Emitter Saturation Voltage ($I_C = 5$ mAdc; $I_B = 0.25$ mAdc)	$V_{BE \text{ (SAT)}}$	-	0.22	0.40	Vdc
DC Current Transfer Ratio ($I_C = 5$ mAdc; $V_{CE} = 0.35$ Vdc)	h_{FE}	20	65	-	-
DC Collector-Emitter Punch-Through Voltage (V_{CB} necessary to obtain V_{EB} of -1 V max, using instrument with $Z_{in} > 11$ megohm to measure V_{BE})	V_{PT}	105	160	-	Vdc
Small-Signal Short-Circuit, Forward Current Transfer Ratio Cutoff Frequency ($V_{CB} = 6$ Vdc; $I_E = 1$ mAdc)	$f_{\alpha b}$	-	1.0	-	MHz

2N398 (continued)

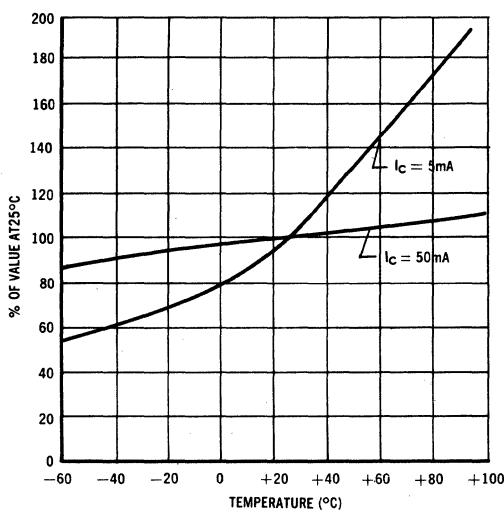
POWER — TEMPERATURE DERATING CURVE



DC CURRENT TRANSFER RATIO versus COLLECTOR CURRENT
 $V_{CE} = 0.35V$



LARGE SIGNAL CURRENT GAIN (H_{FE}) versus TEMPERATURE
(Normalized to 25°C Value; $V_{CE} = 0.35V$)



OUTPUT CURRENT versus BASE-DRIVE VOLTAGE
 $(V_{CE} = -1\text{ V})$

